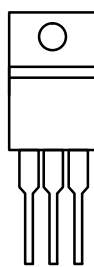


N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
100	0.010 at $V_{GS} = 10$ V	85 ^d	77

TO-220AB



G D S

Top View

Ordering Information:

SUP85N10-10P-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

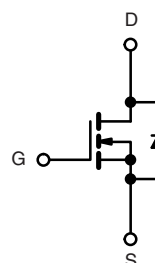
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Industrial



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
Pulsed Drain Current	I_{DM}	240	
Avalanche Current	I_{AS}	60	
Single Avalanche Energy ^a	E_{AS}	180	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	W
		$T_A = 25$ °C ^c	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.55	

Notes:

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

d. Package limited.

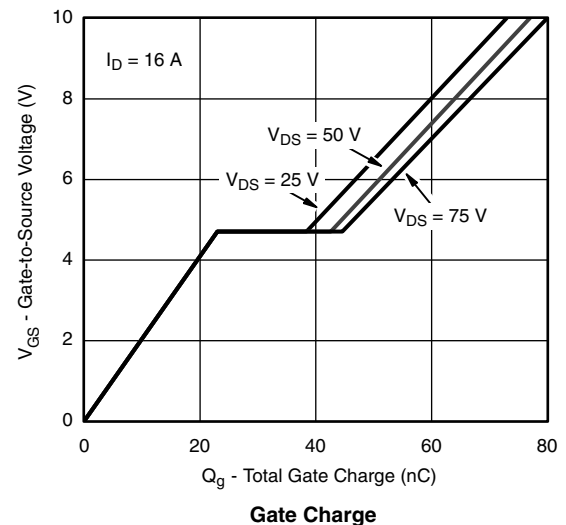
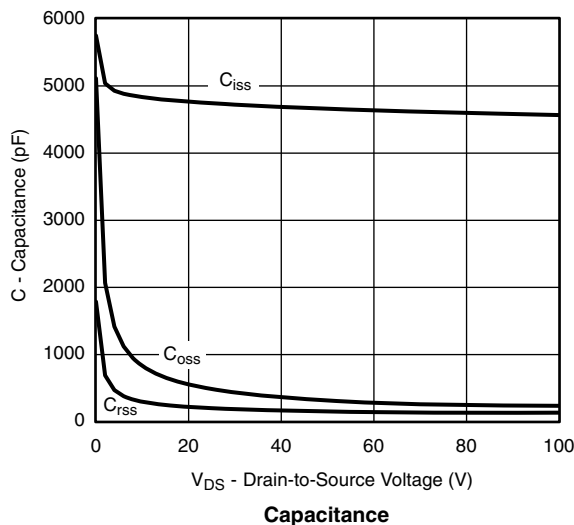
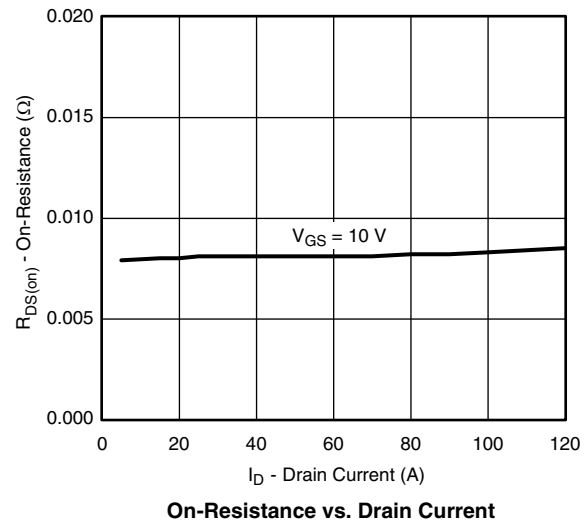
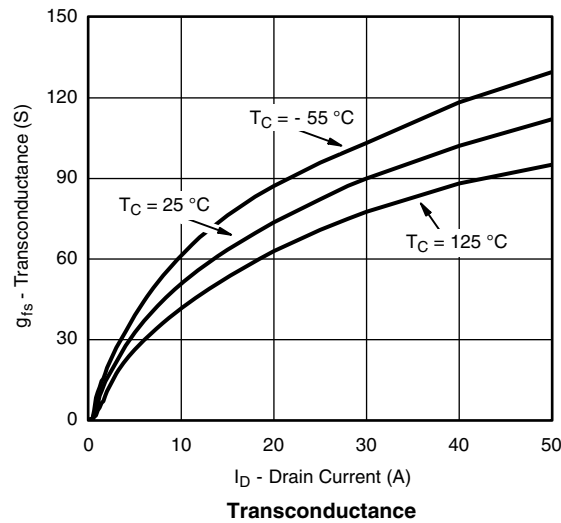
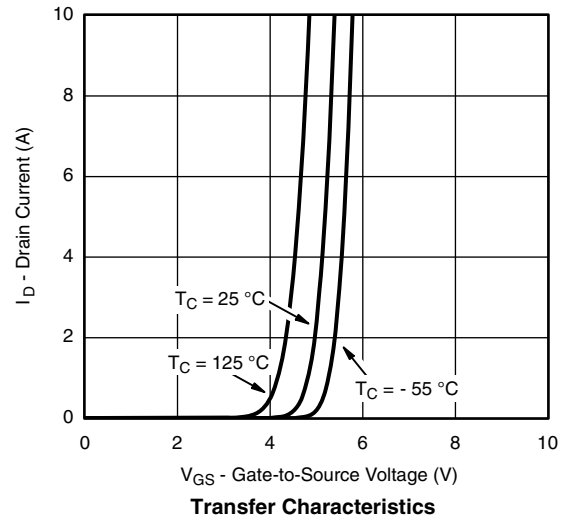
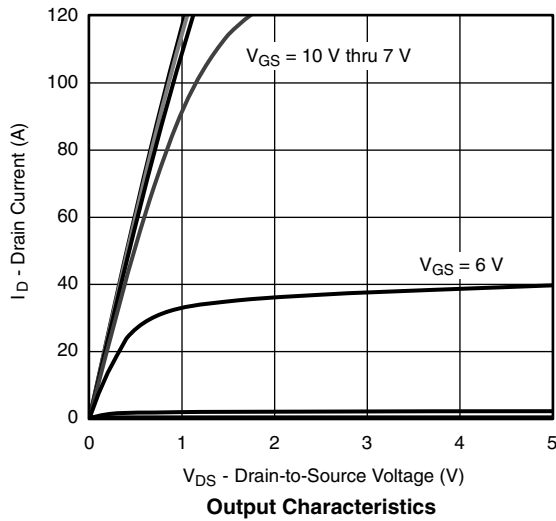
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = 250 μA	100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0080	0.0100	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.0146	0.0185	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A		70		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz		4660		pF
Output Capacitance	C _{oss}			315		
Reverse Transfer Capacitance	C _{rss}			150		
Total Gate Charge ^c	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 75 A		77	120	nC
Gate-Source Charge ^c	Q _{gs}			25		
Gate-Drain Charge ^c	Q _{gd}			20		
Gate Resistance	R _g	f = 1 MHz	0.25	1.2	2.4	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 50 V, R _L = 0.67 Ω I _D ≅ 75 A, V _{GEN} = 10 V, R _g = 1 Ω		15	25	ns
Rise Time ^c	t _r			12	20	
Turn-Off Delay Time ^c	t _{d(off)}			25	40	
Fall Time ^c	t _f			8	15	
Drain-Source Body Diode Characteristics T _C = 25 °C ^b						
Continuous Current	I _S				85	A
Pulsed Current	I _{SM}				240	
Forward Voltage ^a	V _{SD}	I _F = 5 A, V _{GS} = 0 V		0.8	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 5 A, dI/dt = 100 A/μs		74	115	ns
Peak Reverse Recovery Current	I _{RM(REC)}			6.7	10	A
Reverse Recovery Charge	Q _{rr}				250	400

Notes:

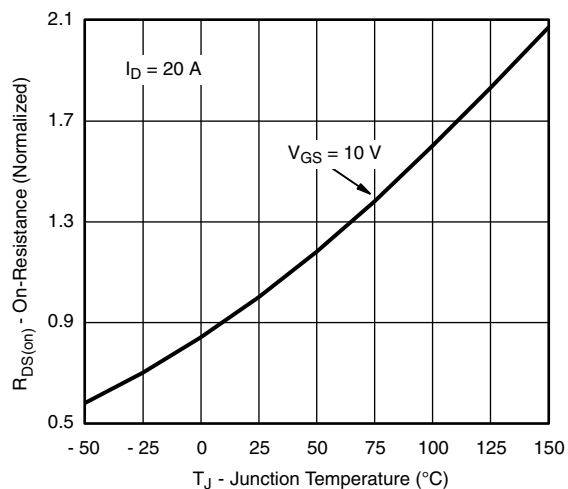
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

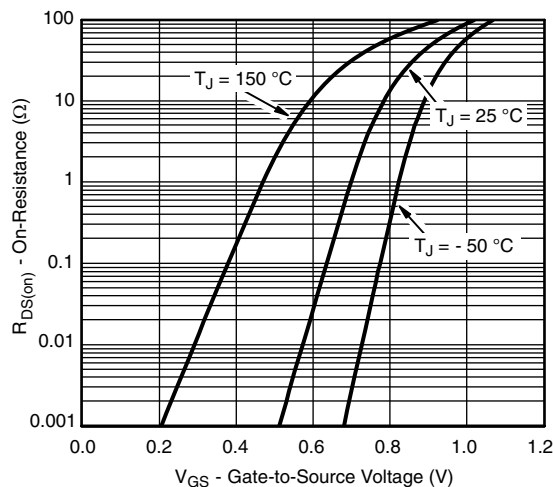
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



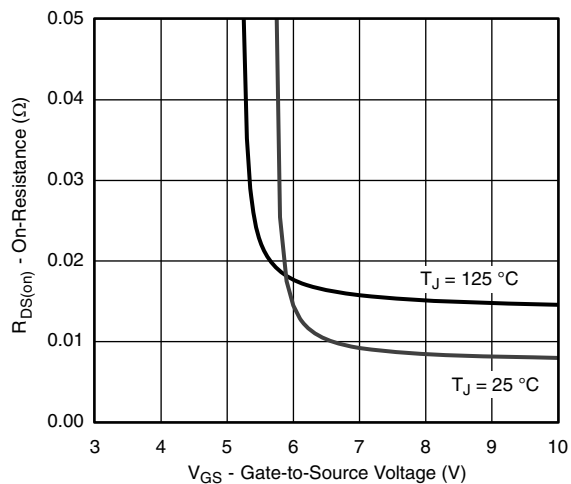
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



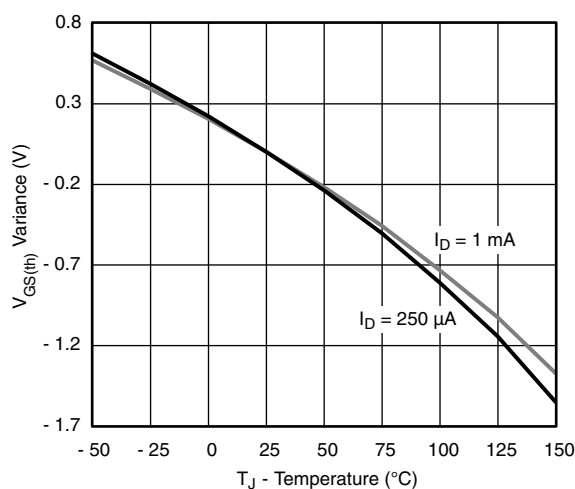
On-Resistance vs. Junction Temperature



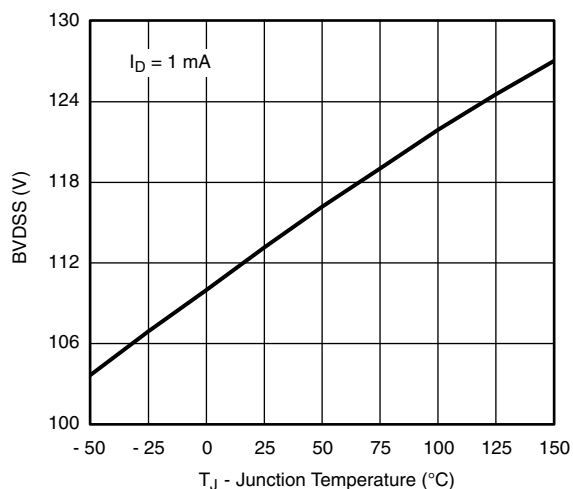
Source-Drain Diode Forward Voltage



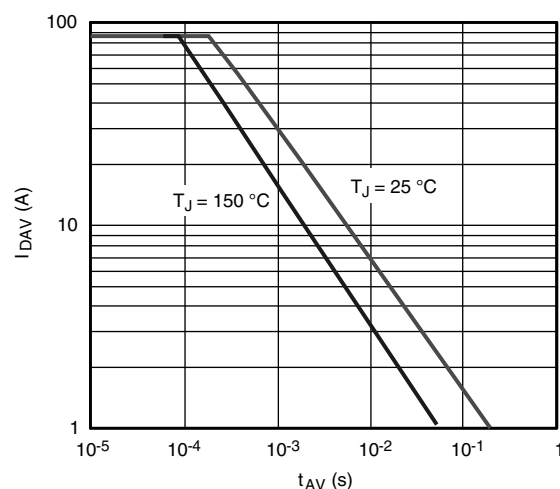
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

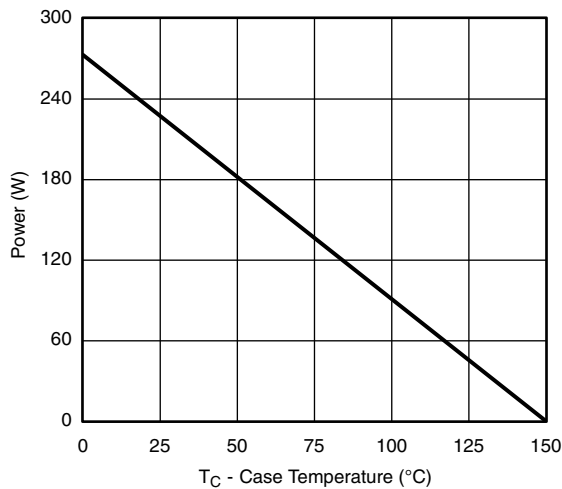
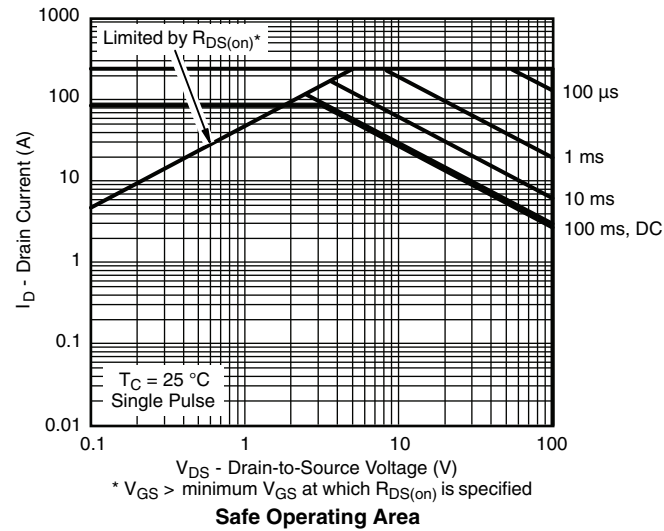


Drain Source Breakdown Voltage vs. Junction Temperature

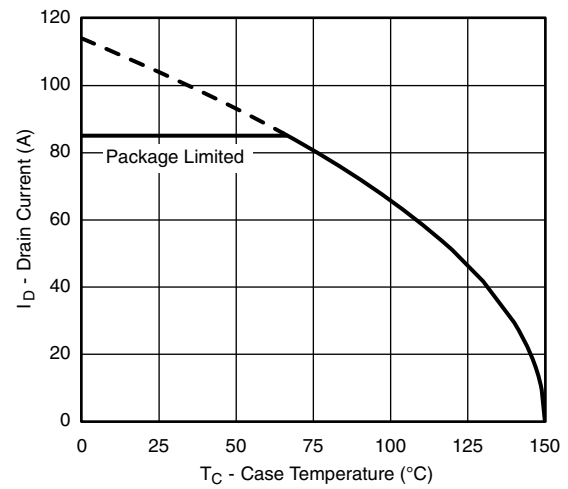


Single Pulse Avalanche Current Capability vs. Time

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



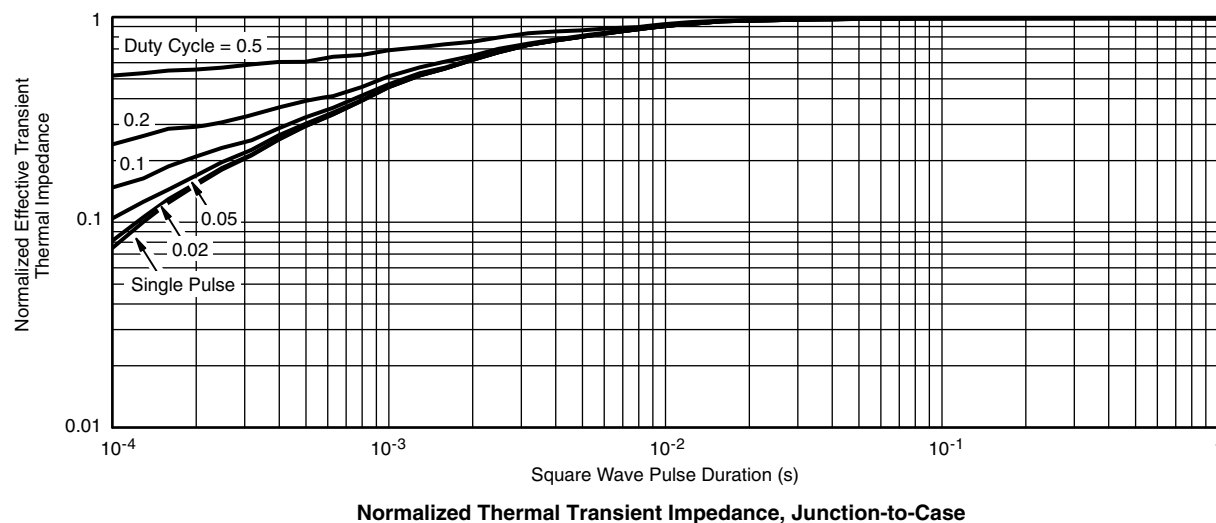
Power Derating, Junction-to-Case



Current Derating*

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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